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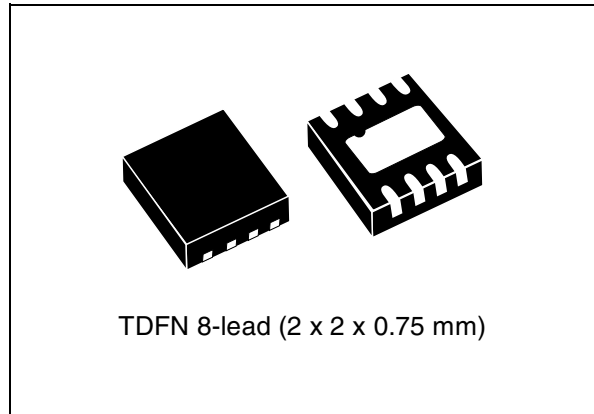


Overvoltage protection device

Datasheet - production data

Features

- Input overvoltage protection up to 28 V
- Integrated high voltage N-channel MOSFET switch - low $R_{DS(on)}$ of 170 m Ω
- Integrated charge pump
- Maximum continuous current of 1.2 A
- Thermal shutdown
- Soft-start feature to control the inrush current
- Enable input (\overline{EN})
- Fault indication output (\overline{FLT})
- IN input ESD protection: ± 15 kV air discharge, ± 8 kV contact discharge (with 1 μ F input capacitor), ± 2 kV HBM (standalone device)
- Certain overvoltage options compliant with the China Communications Standard YD/T 1591-2006 (overvoltage protection only)
- Small, RoHS compliant 2 x 2 x 0.75 mm TDFN 8-lead package with thermal pad.

**Applications**

- Smart phones
- Digital cameras
- PDA and palmtop devices
- MP3 players
- Low power handheld devices.

Contents

- 1 Description 6**
- 2 Pin description 7**
 - 2.1 Input (IN) 7
 - 2.2 Output (OUT) 7
 - 2.3 Fault indication output ($\overline{\text{FLT}}$) 7
 - 2.4 Enable input ($\overline{\text{EN}}$) 7
 - 2.5 No connect (NC) 8
 - 2.6 Ground (GND) 8
- 3 Operation 10**
 - 3.1 Power-up 10
 - 3.2 Normal operation 10
 - 3.3 Undervoltage lockout (UVLO) 10
 - 3.4 Overvoltage lockout (OVLO) 10
 - 3.5 Thermal shutdown 11
- 4 Timing diagrams 12**
- 5 Typical operating characteristics 14**
 - Typical operating characteristics (STBP110GT) 14
- 6 Maximum rating 27**
- 7 DC and AC parameters 28**
- 8 Application information 30**
 - 8.1 Calculating the power dissipation 30
 - 8.2 Calculating the junction temperature 30
 - 8.3 PCB layout recommendations 31
- 9 Package mechanical data 32**
- 10 Tape and reel information 34**

11 Part numbering 37

12 Package marking information 38

13 Revision history 39

List of tables

Table 1.	Pin description and signal names	8
Table 2.	Absolute maximum ratings	27
Table 3.	Thermal data	27
Table 4.	Operating and AC measurement conditions	28
Table 5.	DC and AC characteristics	28
Table 6.	Package mechanical dimensions for TDFN 8-lead (2 x 2 x 0.75 mm)	33
Table 7.	Carrier tape dimensions	34
Table 8.	Further tape and reel information	34
Table 9.	Reel dimensions	35
Table 10.	Ordering information scheme	37
Table 11.	Marking description	38
Table 12.	Document revision history	39

List of figures

Figure 1.	Logic diagram	6
Figure 2.	Pinout	6
Figure 3.	Block diagram	9
Figure 4.	Typical application circuit	9
Figure 5.	Power-up	12
Figure 6.	Overshoot protection	12
Figure 7.	Disable (\overline{EN} = high).	12
Figure 8.	Recovery from OVP	13
Figure 9.	Maximum MOSFET current at $T_A = 85\text{ }^\circ\text{C}$ for various PCB thermal performance and $T_J \leq 125\text{ }^\circ\text{C}$	14
Figure 10.	Startup, t_{on}	14
Figure 11.	Overshoot, t_{off}	15
Figure 12.	Recovery from overshoot, t_{rec}	15
Figure 13.	Disable, t_{dis}	16
Figure 14.	Startup to overshoot.	16
Figure 15.	Startup to overshoot (detail).	17
Figure 16.	Soft-start performance for 10 μF capacitive load	17
Figure 17.	Soft-start performance for 100 μF capacitive load	18
Figure 18.	I_{CC} vs. temperature at $V_{IN} = 5\text{ V}$	18
Figure 19.	I_{CC} vs. V_{IN}	19
Figure 20.	I_{CC} vs. V_{IN} (detail)	19
Figure 21.	$I_{CC(STDBY)}$ vs. temperature at $V_{IN} = 5\text{ V}$	20
Figure 22.	$I_{CC(STDBY)}$ vs. V_{IN}	20
Figure 23.	$I_{CC(STDBY)}$ vs. V_{IN} (detail)	21
Figure 24.	V_{OVLO} vs. temperature	21
Figure 25.	V_{UVLO} vs. temperature	22
Figure 26.	$V_{OL(\overline{FLT})}$ vs. temperature at $I_{SINK(\overline{FLT})} = 5\text{ mA}$, $V_{IN} = 5\text{ V}$	22
Figure 27.	$R_{DS(on)}$ vs. temperature at 5 V, 1 A	23
Figure 28.	$V_{IL(\overline{EN})}$ vs. temperature	23
Figure 29.	$V_{IH(\overline{EN})}$ vs. temperature	24
Figure 30.	$I_{(\overline{EN})}$ vs. V_{IN} at $V_{(\overline{EN})} = 5\text{ V}$	24
Figure 31.	$R_{PD(\overline{EN})}$ vs. temperature at $V_{(\overline{EN})} = V_{IN} = 5\text{ V}$	25
Figure 32.	t_{on} vs. temperature	25
Figure 33.	t_{rec} vs. temperature	26
Figure 34.	Package mechanical drawing for TDFN 8-lead (2 x 2 x 0.75 mm)	32
Figure 35.	Tape and reel	34
Figure 36.	Reel dimensions	35
Figure 37.	Tape trailer/leader.	35
Figure 38.	Pin 1 orientation	36

1 Description

The STBP110 device provides overvoltage protection for input voltage up to +28 V. Its low $R_{DS(on)}$ N-channel MOSFET switch protects the systems connected to the OUT pin against failures of the DC power supplies in accordance with the China MII Communications Standard YD/T 1591-2006.

In the event of an input overvoltage condition, the device immediately disconnects the DC power supply by turning off an internal low $R_{DS(on)}$ N-channel MOSFET to prevent damage to protected components.

In addition, the device also monitors its own junction temperature and switches off the internal MOSFET if the junction temperature exceeds the specified limit.

The device can be controlled by the microcontroller and can also provide status information about fault conditions.

The STBP110 is offered in a small, RoHS-compliant 8-lead TDFN (2 mm x 2 mm) package.

Figure 1. Logic diagram

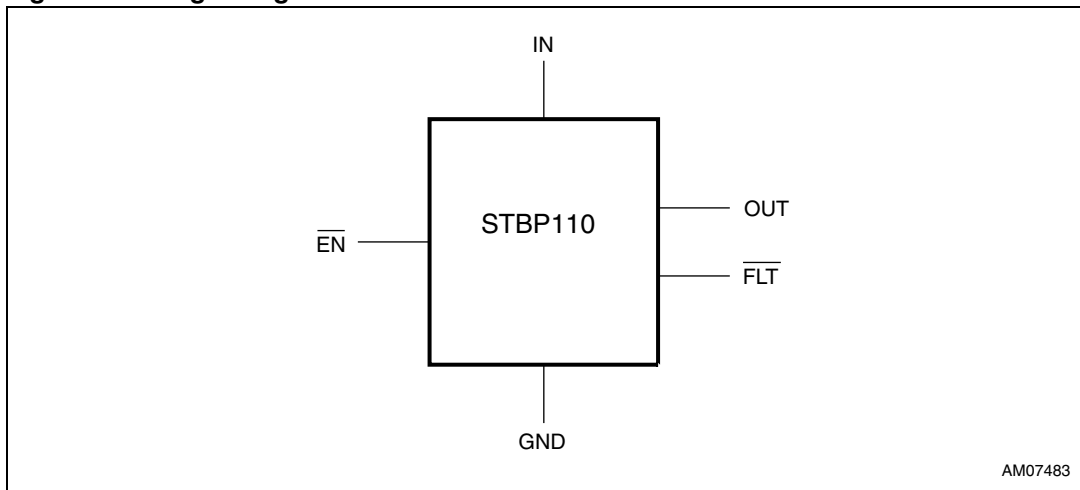
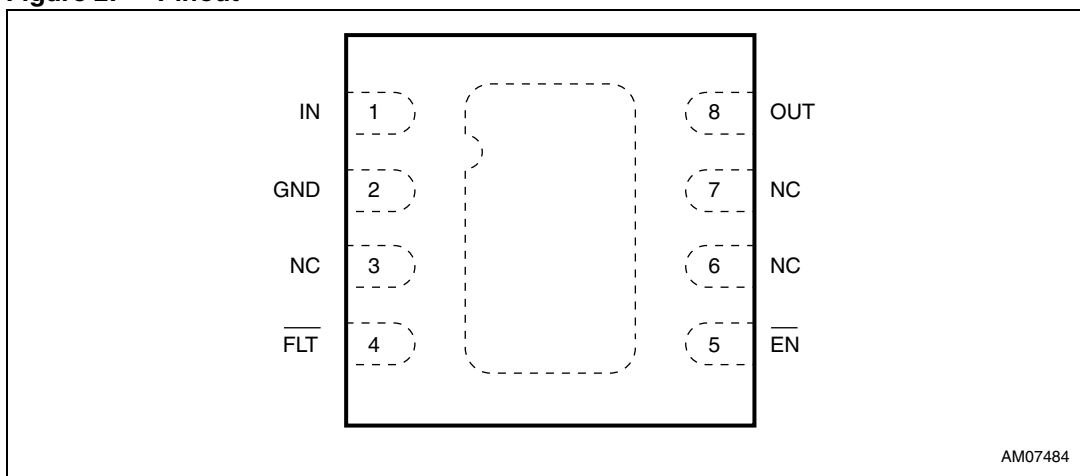


Figure 2. Pinout



1. Exposed thermal pad may be tied to GND.

2 Pin description

2.1 Input (IN)

Input voltage (IN) pin. The IN pin is connected to the DC power supply. An external low ESR ceramic capacitor of minimum value 1 μF must be connected between IN and GND. This capacitor is needed for decoupling and also protects the IC against fast voltage spikes and ESD events. This capacitor should be located as close to the IN pin as possible.

2.2 Output (OUT)

Output voltage (OUT) pin. The OUT pin is connected to the input through a low $R_{\text{DS(on)}}$ N-channel MOSFET switch.

If no fault is detected and the STBP110 is enabled by the $\overline{\text{EN}}$ input, this switch is turned on and the output voltage follows the input voltage.

The output is disconnected from the input when the input voltage is under the UVLO threshold or above the OVLO threshold, when the junction temperature is above the thermal shutdown threshold or when the device is disabled by the $\overline{\text{EN}}$ input.

After the input voltage or junction temperature returns to the specified range, there is a recovery delay, t_{rec} , and the power output is then connected to the input (see [Figure 8](#)).

The switch turn-on time is intentionally prolonged to limit the inrush current and voltage drop caused, for example, by charging output capacitors (soft-start feature).

2.3 Fault indication output ($\overline{\text{FLT}}$)

The active low, open-drain fault indication output provides information on the STBP110 state to the application controller. The $\overline{\text{FLT}}$ is asserted (i.e. driven low), if the STBP110 is in the overvoltage condition or thermal shutdown mode is active.

As the $\overline{\text{FLT}}$ output is of the open-drain type, it may be pulled up by an external resistor R_{PU} to the controller supply voltage (see [Figure 4](#)). If there is no need to use this output, it may be left disconnected. The suitable R_{PU} resistor value is in the range of 10 k Ω to 1 M Ω .

To improve safety and to prevent damage to application circuits in the event of extreme voltage or current conditions, an optional protective resistor R_{FLT} can be connected between the $\overline{\text{FLT}}$ output and the controller input (see [Figure 4](#)). The suitable R_{FLT} resistor value is in the range of 10 k Ω to 100 k Ω .

The $\overline{\text{FLT}}$ output is in Hi-Z (high impedance) state when the device is disabled by $\overline{\text{EN}}$ input or when the input voltage is lower than the UVLO threshold.

2.4 Enable input ($\overline{\text{EN}}$)

This active low logical input can be used to enable or disable the device. When the $\overline{\text{EN}}$ input is driven high, the STBP110 is in shutdown mode and the power output is disconnected from the input (see [Figure 8](#)). When the $\overline{\text{EN}}$ input is driven low and all operating conditions are within specified limits, the power output is connected to the input.

The \overline{EN} input is equipped with an internal pull-down resistor of 250 kΩ (typical value). If there is no need to use this input, it may be left floating or, preferably, connected to GND.

For V_{IN} lower than 2.5 V (max.), the pull-down resistor is internally disconnected to lower the \overline{EN} pin input current in case the external AC adapter is not connected, the application is running from an internal battery and the STBP110 device is disabled.

To improve safety and to prevent damage to application circuits in the event of extreme voltage or current conditions, an optional protective resistor R_{EN} can be connected between the \overline{EN} input and the controller output (see *Figure 4*). The protective resistor forms a voltage divider with the internal pull-down resistor, which limits the maximum possible R_{EN} value with respect to the $V_{IH}(\overline{EN})$ threshold of \overline{EN} input and the controller's output voltage for logic high, V_{OH} . For the worst case, the highest protective resistor value is

$$R_{ENmax} = R_{PD}(\overline{EN})_{min} \times (V_{OH} / V_{IH}(\overline{EN}) - 1),$$

where $R_{PD}(\overline{EN})_{min}$ is 100 kΩ and $V_{IH}(\overline{EN})$ is 1.2 V.

For most cases, an R_{EN} value of 10 kΩ to 100 kΩ is adequate.

The \overline{FLT} output is in Hi-Z state when the device is disabled by \overline{EN} input.

2.5 No connect (NC)

Pin 3, 6, and 7 are no connect (NC). They may be left floating or connected to GND.

2.6 Ground (GND)

Ground terminal. All voltages are referenced to GND. The exposed thermal pad is internally connected to GND.

Table 1. Pin description and signal names

Pin	Name	Type	Function
1	IN	Input/supply	Input voltage
2	GND	Supply	Ground
3, 6, 7	NC	-	Not connected
4	\overline{FLT}	Output	Fault indication output (open-drain)
5	\overline{EN}	Input	Enable input (pull-down resistor to GND)
8	OUT	Output	Output voltage

Figure 3. Block diagram

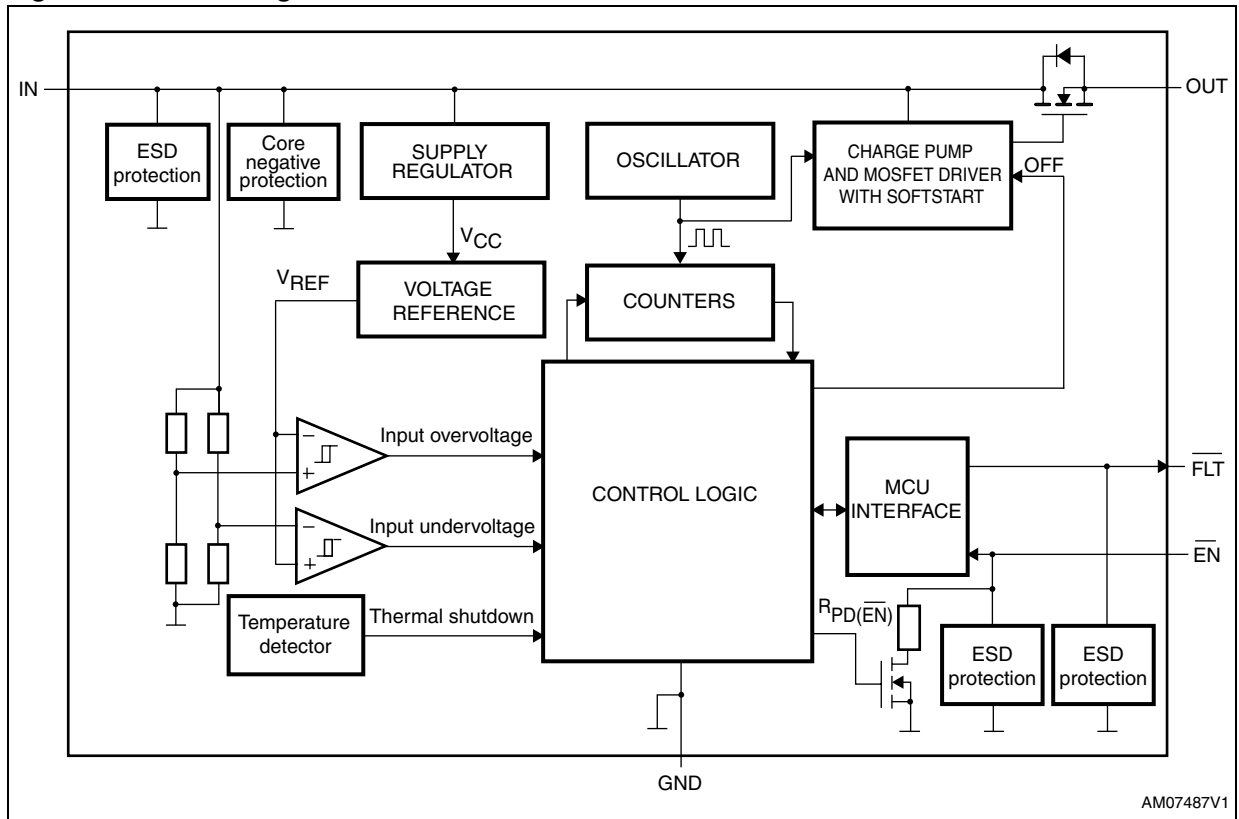
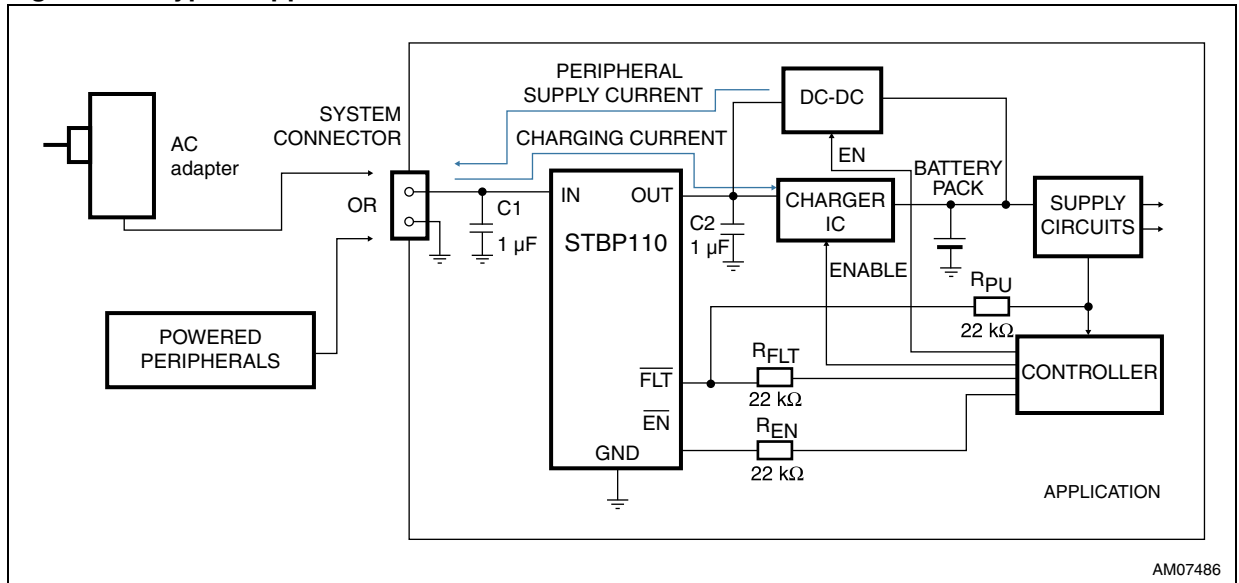


Figure 4. Typical application circuit



1. Optional resistors R_{EN} and R_{FLT} prevent damage to the controller under extreme voltage or current conditions and are not required. Low ESR ceramic capacitor C1 is necessary to ensure proper function of the STBP110. Capacitor C2 is not necessary for STBP110 but may be required by the charger IC.
2. The STBP110 MOSFET switch topology allows the current to flow also in a reverse direction, i.e. from OUT to IN, which can be useful for powering external peripherals from the system connector. If the reverse current (supply current) is undesirable, it may be prevented by connecting an external Schottky diode in series with the OUT pin. The voltage drop between IN and the charger is then increased by the voltage drop across the diode.

3 Operation

The STBP110 provides overvoltage protection for positive input voltage up to 28 V using a built-in low $R_{DS(on)}$ N-channel MOSFET switch.

3.1 Power-up

At power-up, with $\overline{EN} = \text{low}$, the MOSFET switch is turned on after the startup delay, t_{on} , after the input voltage exceeds the UVLO threshold to ensure the input voltage is stabilized (see [Figure 5](#)).

3.2 Normal operation

The device continuously monitors the input voltage and its own internal temperature so the output voltage is kept within the specified range. The internal MOSFET switch is turned on and the \overline{FLT} output is deasserted.

The STBP110 enters normal operation state if the input voltage returns to the interval between V_{UVLO} and $V_{OVLO} - V_{HYS(OVLO)}$ and the junction temperature falls below $T_{off} - T_{HYS(off)}$. The internal MOSFET is turned on after the t_{rec} delay to ensure that the conditions have stabilized and the \overline{FLT} output is deasserted.

Note: The STBP110 MOSFET switch topology allows the current to flow also in a reverse direction, i.e. from OUT to IN, which can be useful for powering external peripherals from the system connector (see the supply current in [Figure 4](#)). At first, the current flows through the MOSFET body diode. If the voltage that appears on the IN terminal is above the UVLO threshold, the MOSFET is (after the startup delay) turned on so the voltage drop across STBP110 is significantly reduced. If the reverse current is undesirable, it may be prevented by connecting an external, properly rated low drop Schottky diode in series with the OUT pin. The voltage drop between IN and charger is increased by the voltage drop across the diode.

3.3 Undervoltage lockout (UVLO)

To ensure proper operation under any condition, the STBP110 has an undervoltage lockout (UVLO) threshold. When the input voltage is rising, the output remains disconnected from input until the V_{IN} voltage exceeds the V_{UVLO} threshold. This circuit is equipped with hysteresis, $V_{HYS(UVLO)}$, to improve noise immunity under transient conditions.

3.4 Overvoltage lockout (OVLO)

If the input voltage V_{IN} rises above the threshold level V_{OVLO} , the MOSFET switch is immediately turned off. At the same time, the fault indication output \overline{FLT} is activated (i.e. driven low), see [Figure 6](#). This device is equipped with hysteresis, $V_{HYS(OVLO)}$, to improve noise immunity under transient conditions.

3.5 Thermal shutdown

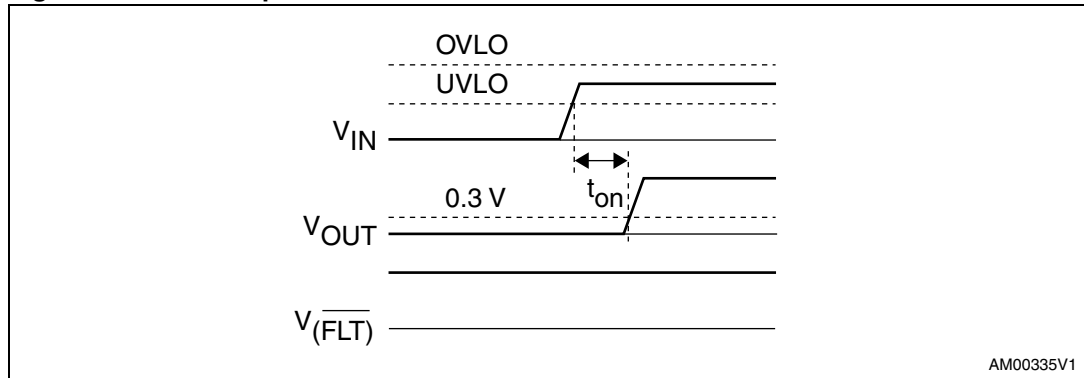
If the STBP110 internal junction temperature exceeds the T_{off} threshold, the internal MOSFET switch is turned off and the fault indication output \overline{FLT} is driven low.

To improve thermal robustness, this circuit has a 20 °C hysteresis, $T_{HYS(off)}$.

Due to the internal reverse diode, the thermal shutdown is not functional for the reverse current.

4 Timing diagrams

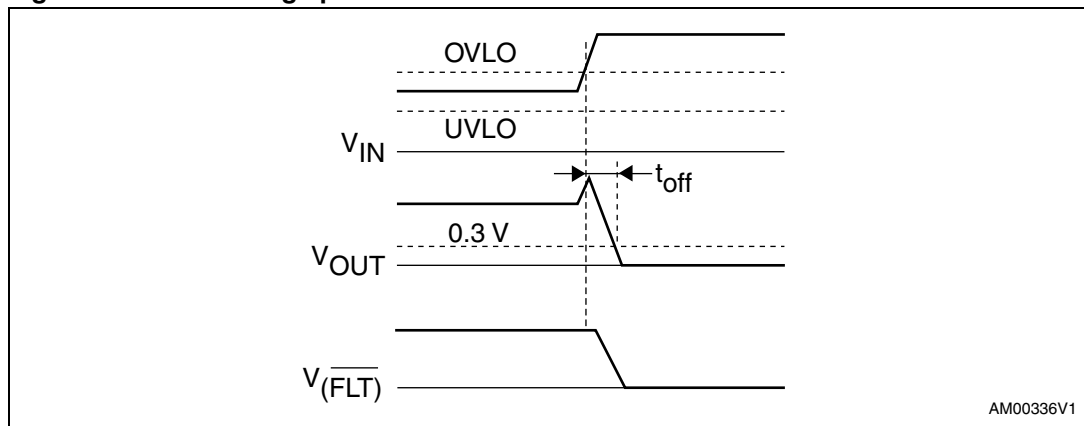
Figure 5. Power-up



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1. \overline{EN} input is low.

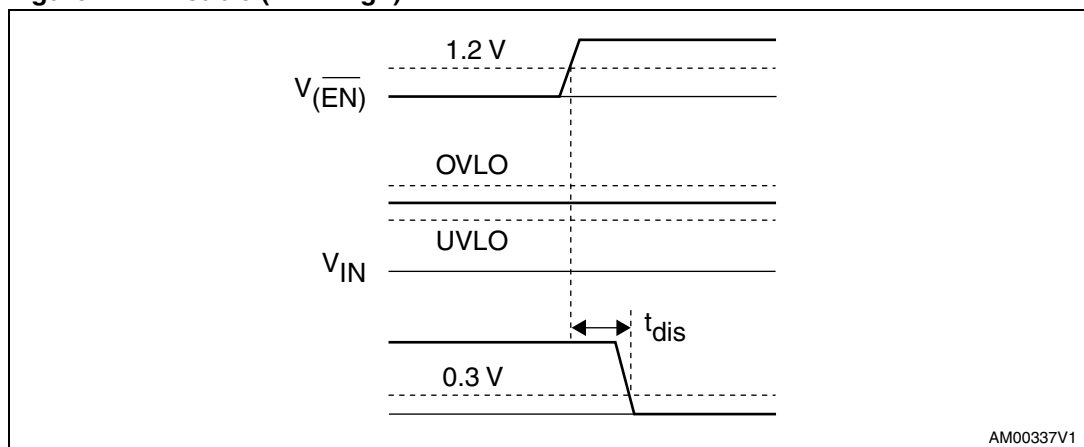
Figure 6. Overvoltage protection



AM00336V1

1. \overline{EN} input is low.

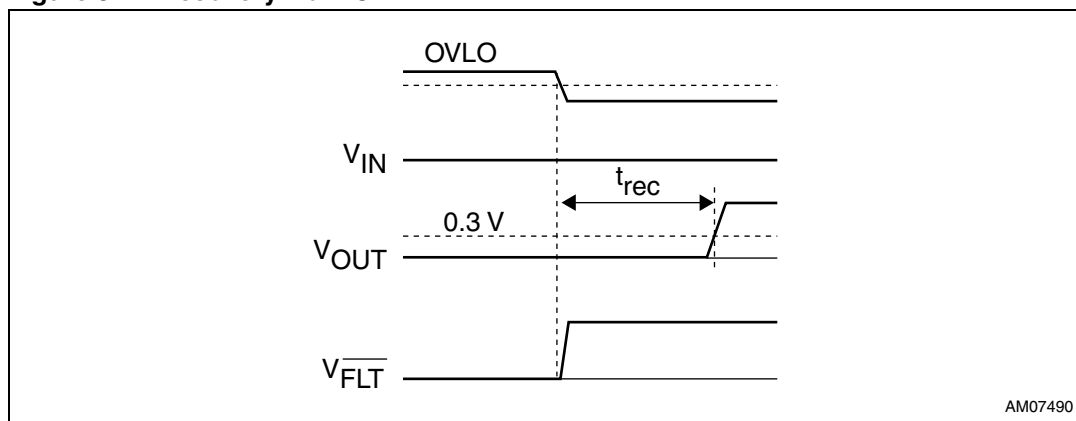
Figure 7. Disable ($\overline{EN} = \text{high}$)



AM00337V1

1. \overline{FLT} output is in Hi-Z state when \overline{EN} driven high.

Figure 8. Recovery from OVP

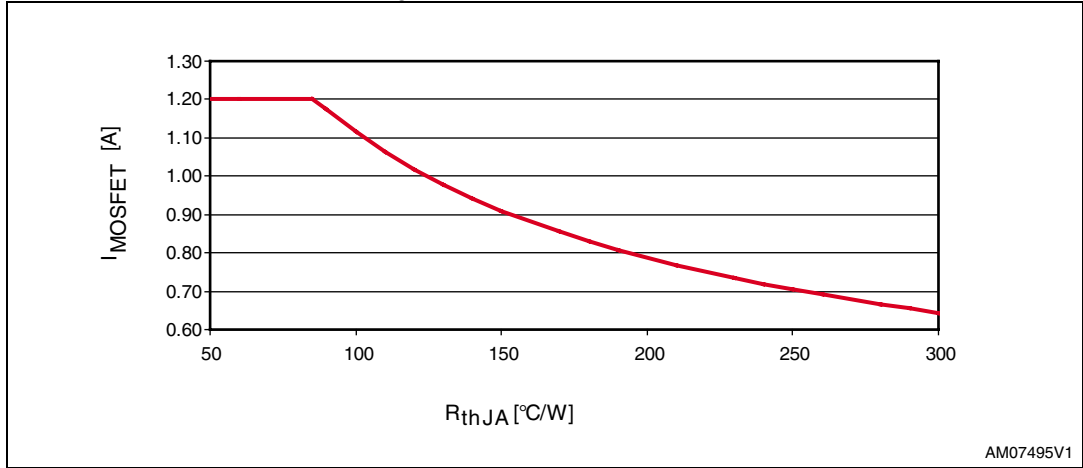


AM07490

1. \overline{EN} input is low.

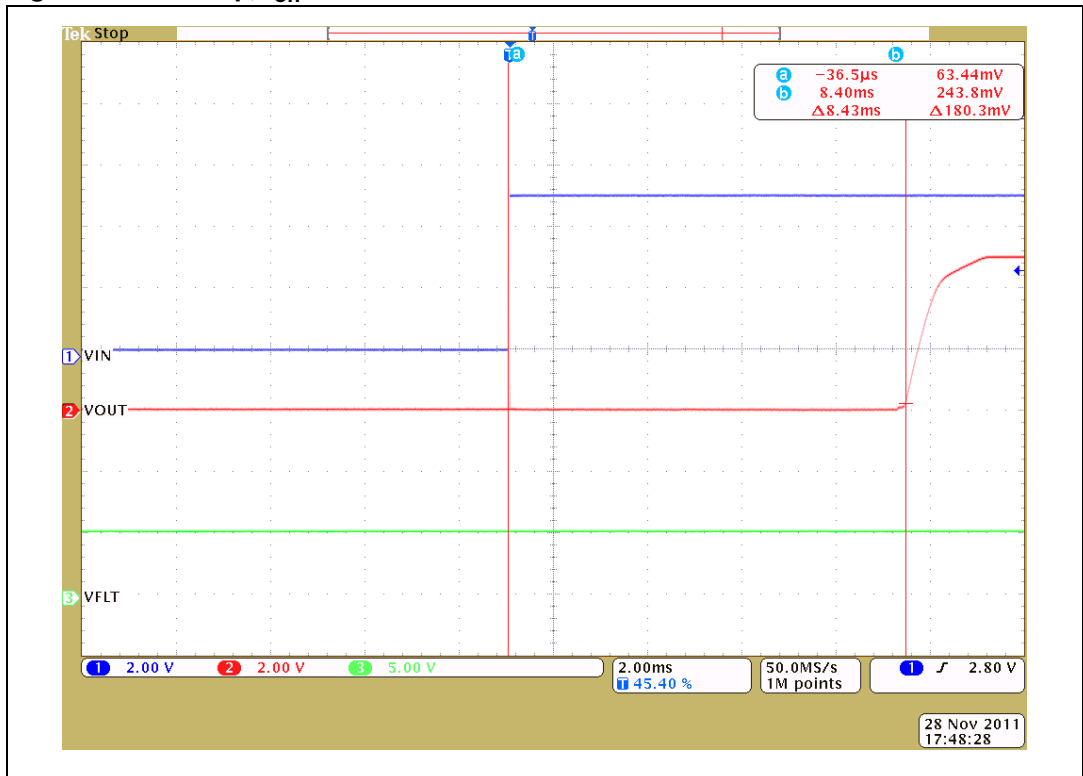
5 Typical operating characteristics

Figure 9. Maximum MOSFET current at $T_A = 85\text{ °C}$ for various PCB thermal performance and $T_J \leq 125\text{ °C}$



Typical operating characteristics (STBP110GT)

Figure 10. Startup, t_{on}



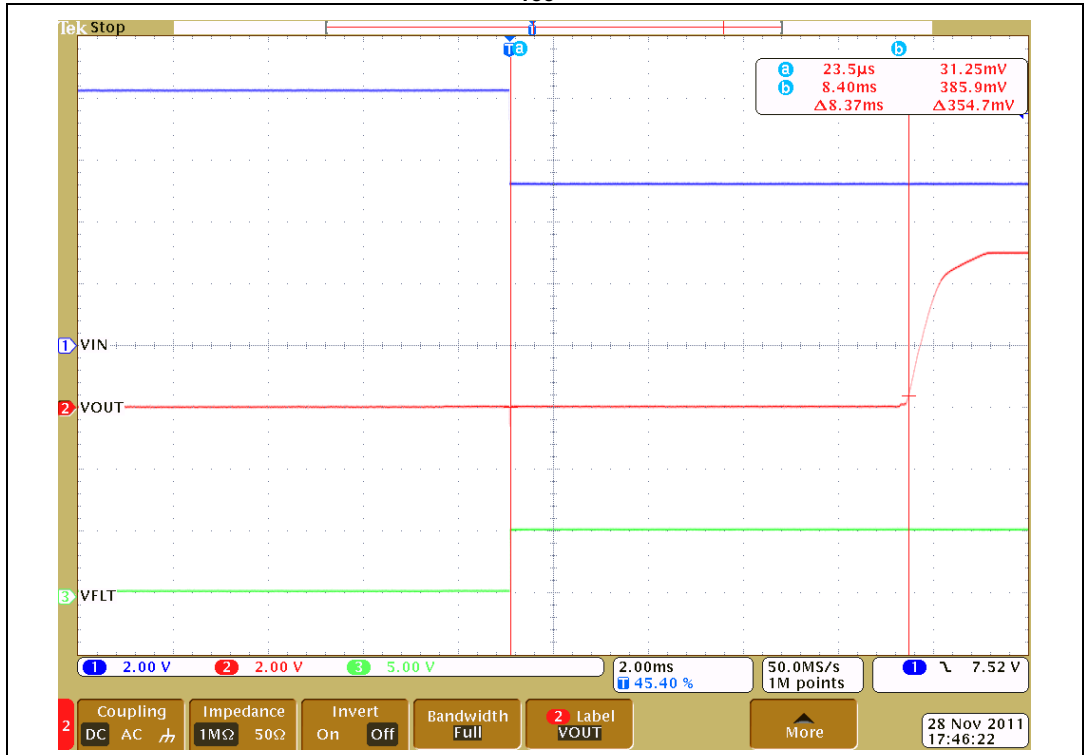
1. Output load is 100 kΩ.

Figure 11. Overvoltage, t_{off}



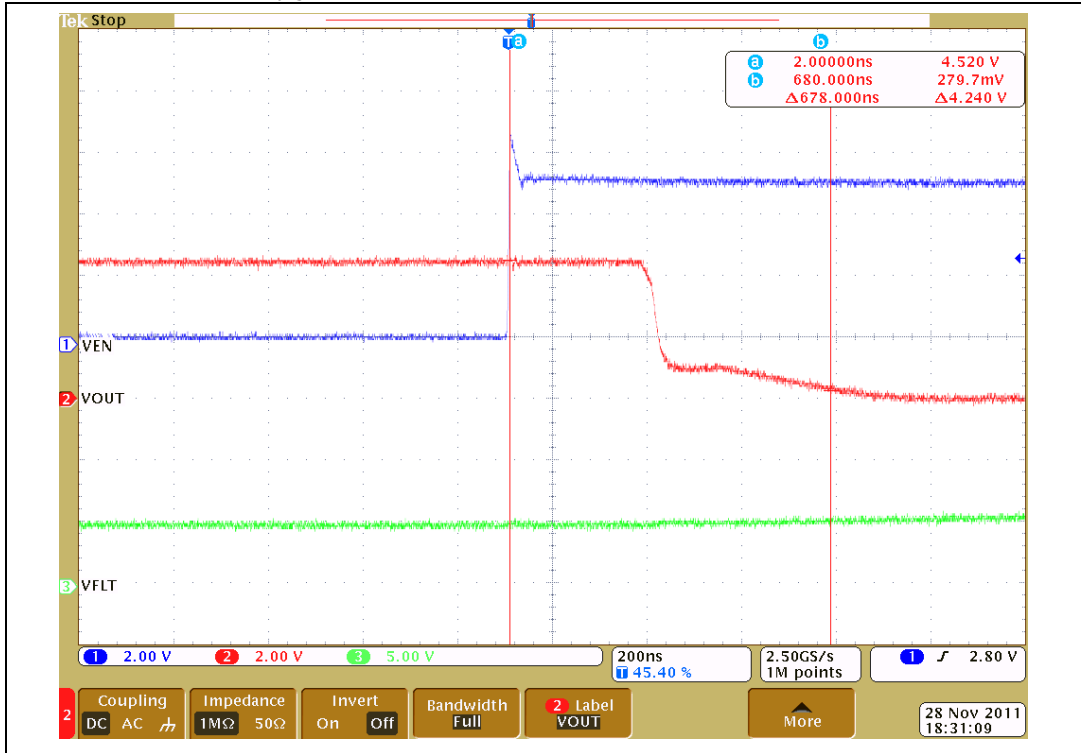
1. Output load is 5 Ω .

Figure 12. Recovery from overvoltage, t_{rec}



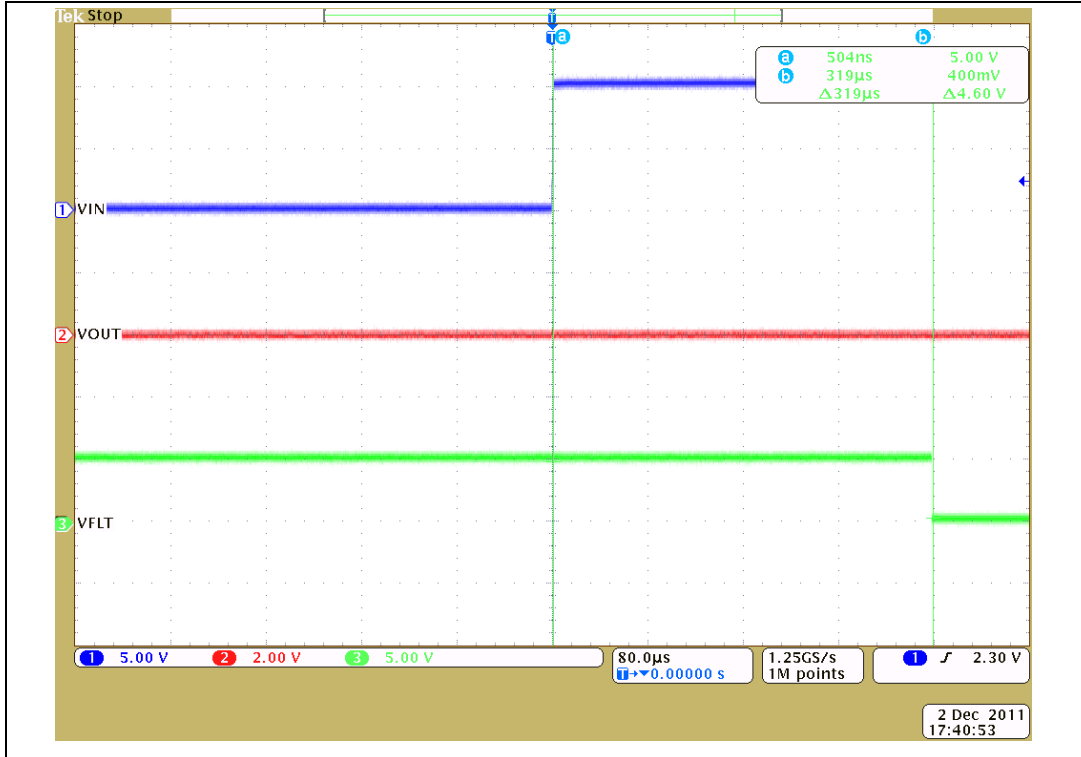
1. Output load is 5 Ω .

Figure 13. Disable, t_{dis}



1. Output load is 5 Ω.

Figure 14. Startup to overvoltage



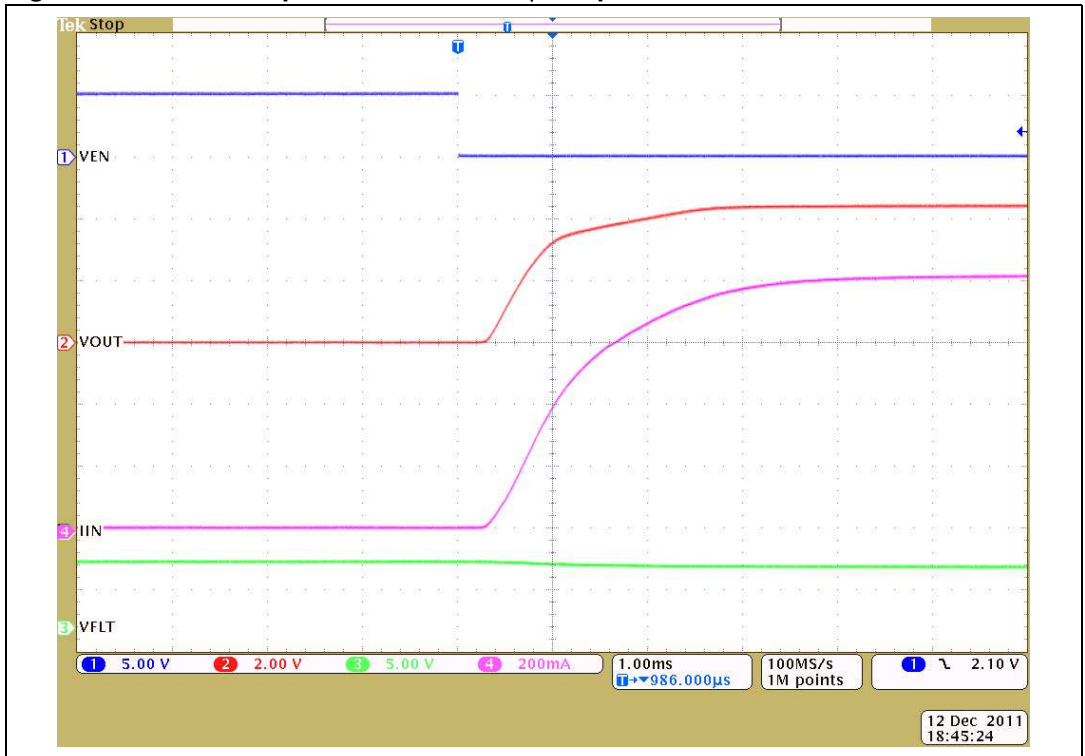
1. Output load is 5 Ω.

Figure 15. Startup to overvoltage (detail)



1. Output load is 5 Ω. Almost no glitch on the output.

Figure 16. Soft-start performance for 10 µF capacitive load



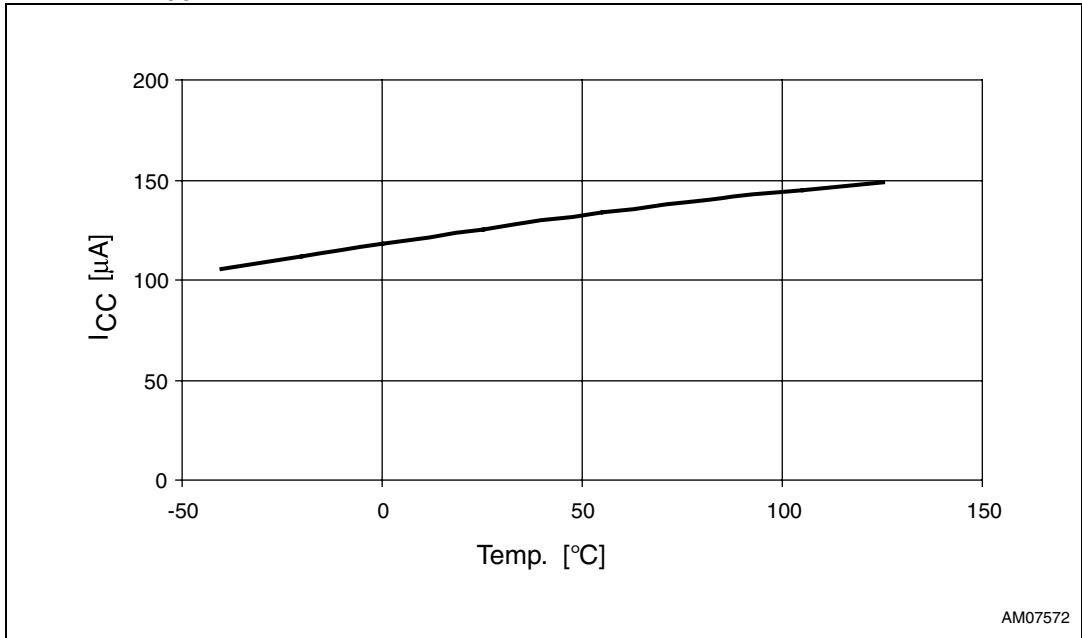
1. Output load is 10 µF in parallel with 5 Ω.

Figure 17. Soft-start performance for 100 μ F capacitive load



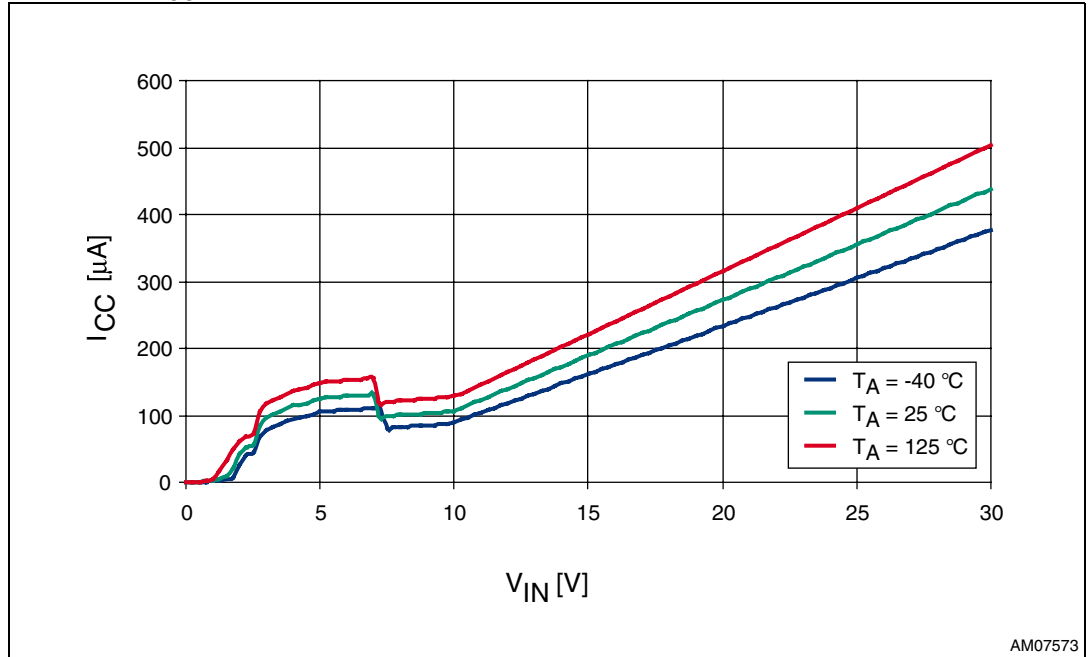
1. Output load is 100 μ F in parallel with 5 Ω .

Figure 18. I_{CC} vs. temperature at $V_{IN} = 5$ V



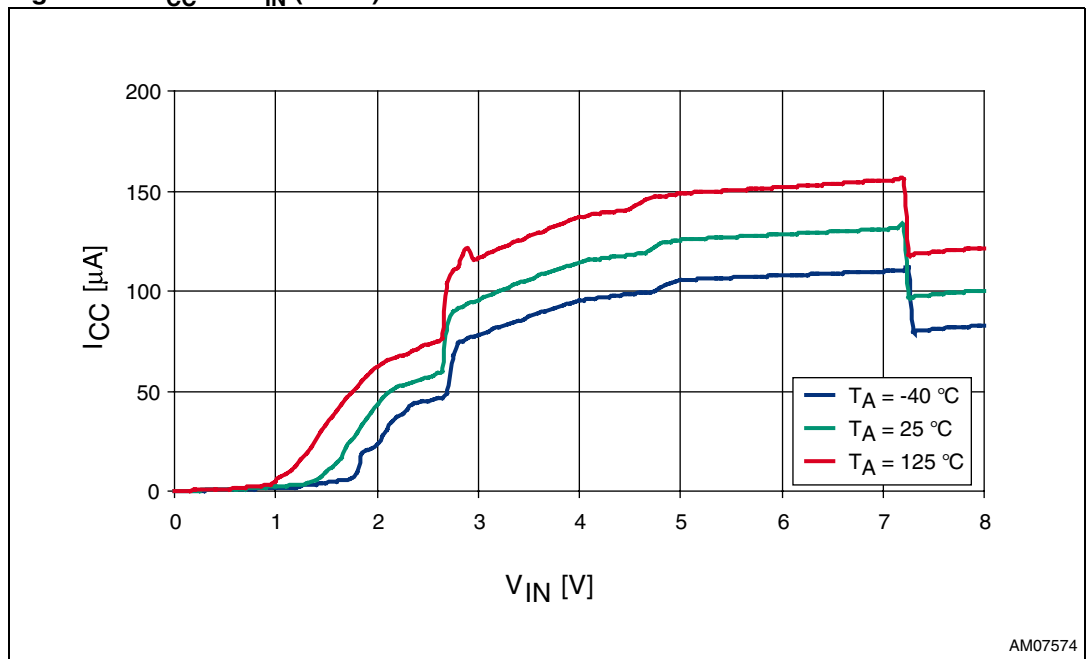
AM07572

Figure 19. I_{CC} vs. V_{IN}



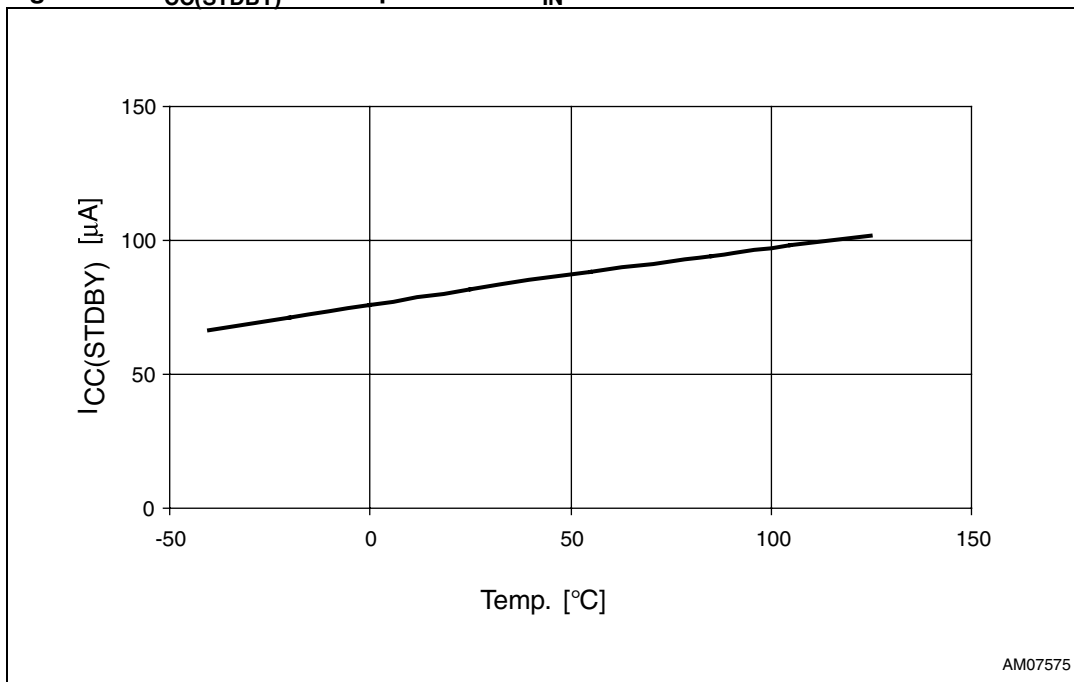
AM07573

Figure 20. I_{CC} vs. V_{IN} (detail)



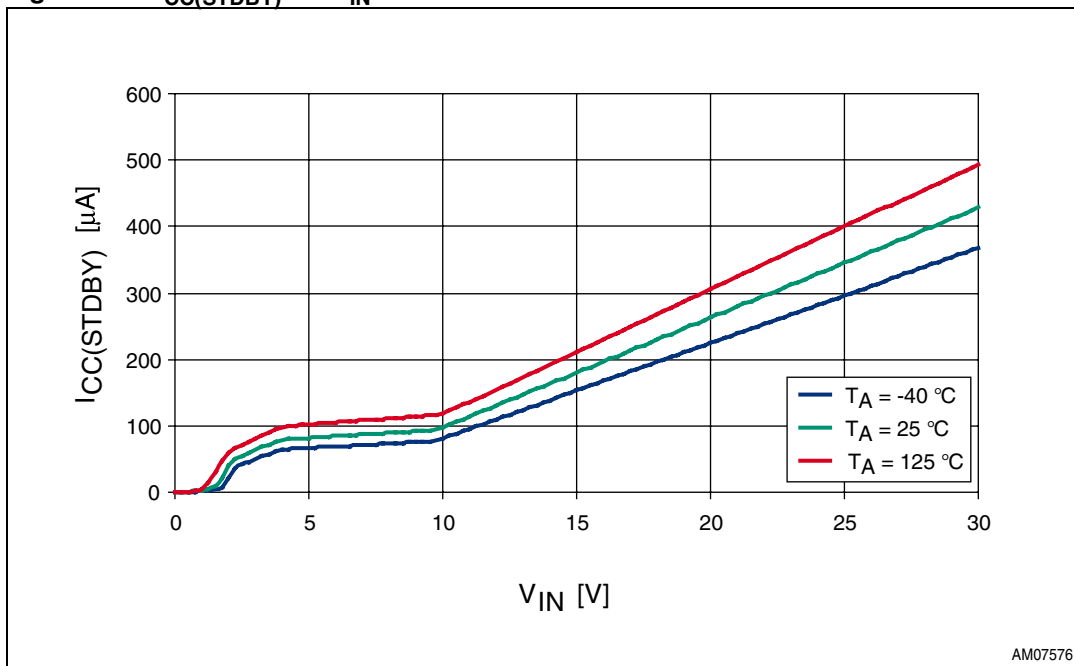
AM07574

Figure 21. $I_{CC(STDBY)}$ vs. temperature at $V_{IN} = 5\text{ V}$



AM07575

Figure 22. $I_{CC(STDBY)}$ vs. V_{IN}



AM07576

Figure 23. $I_{CC(STDBY)}$ vs. V_{IN} (detail)

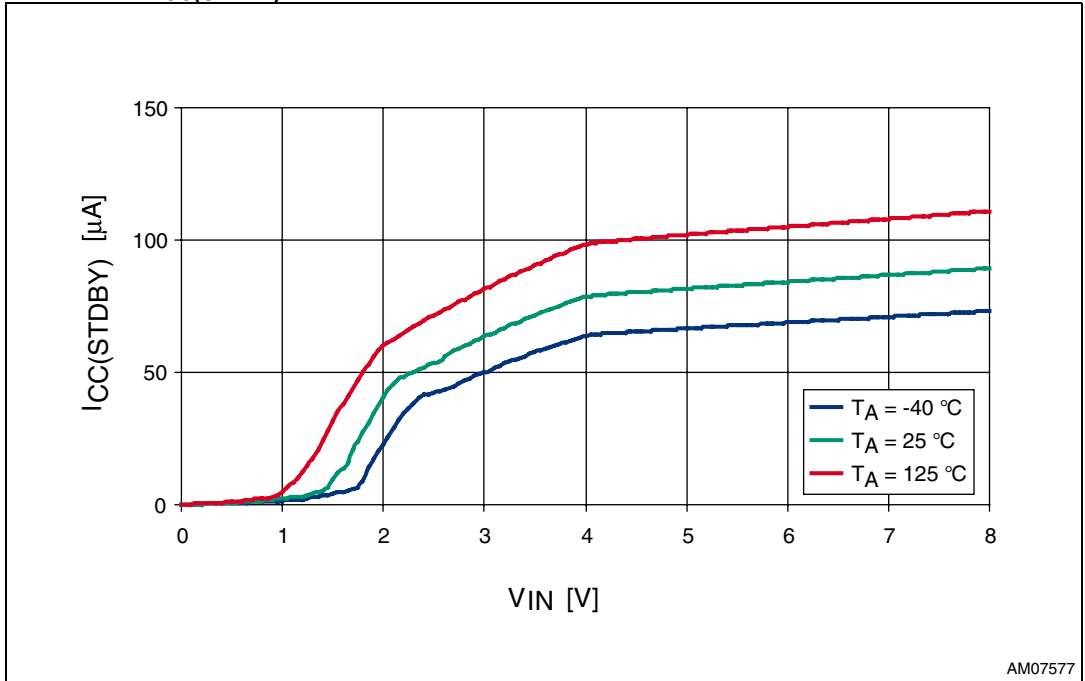


Figure 24. V_{OVLO} vs. temperature

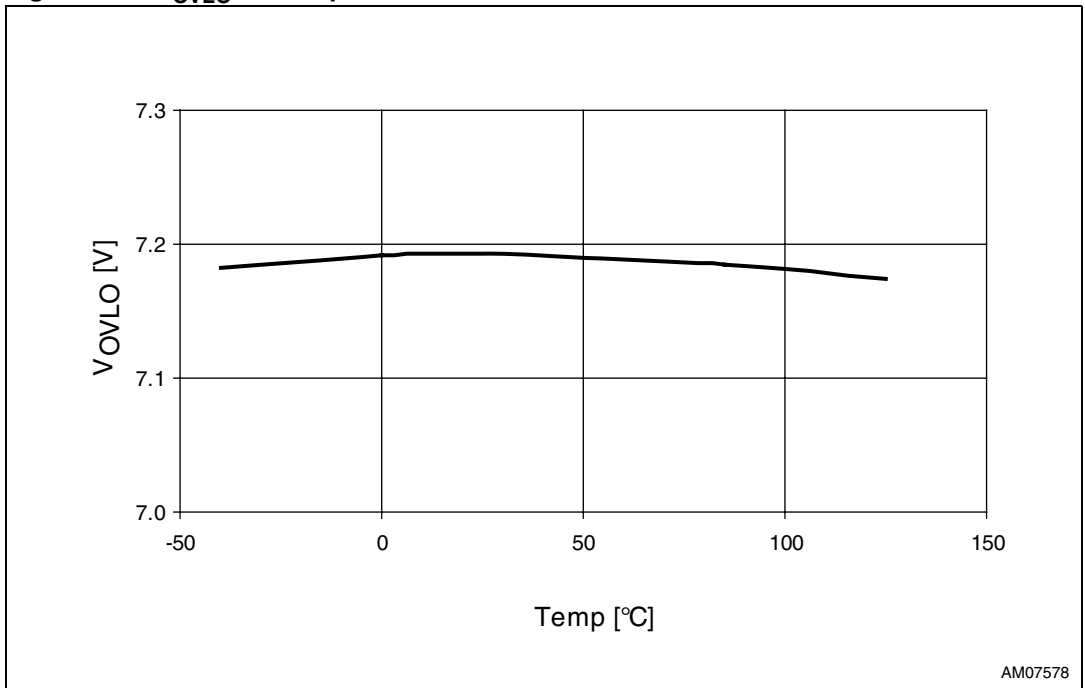


Figure 25. V_{UVLO} vs. temperature

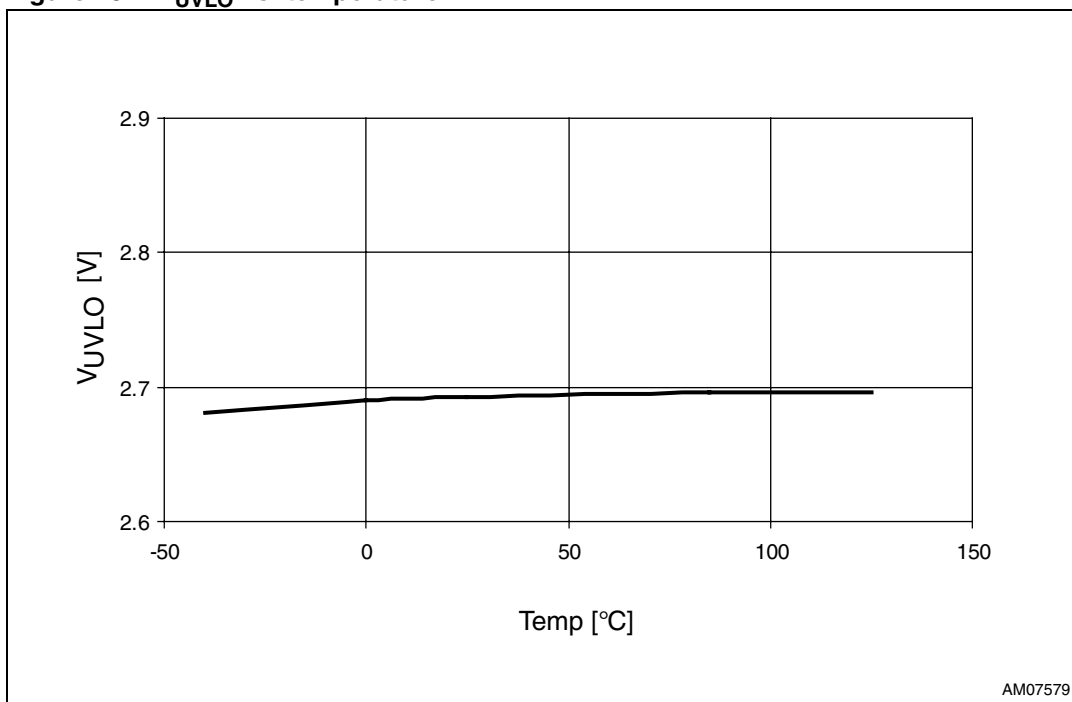


Figure 26. $V_{OL(\overline{FLT})}$ vs. temperature at $I_{SINK(\overline{FLT})} = 5\text{ mA}$, $V_{IN} = 5\text{ V}$

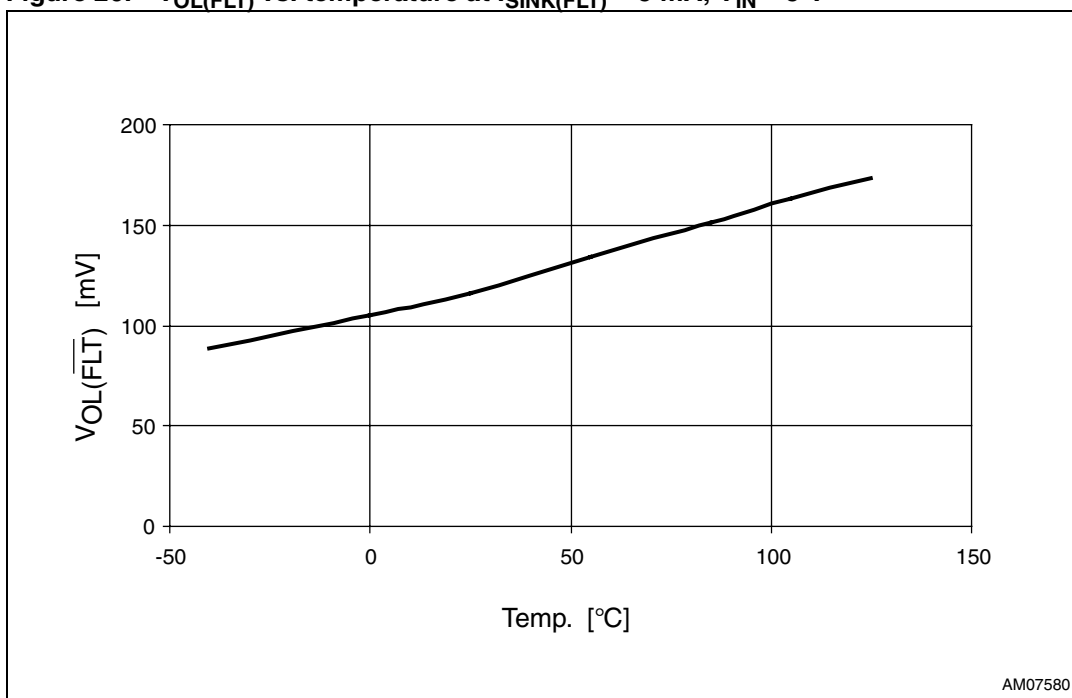


Figure 27. $R_{DS(on)}$ vs. temperature at 5 V, 1 A

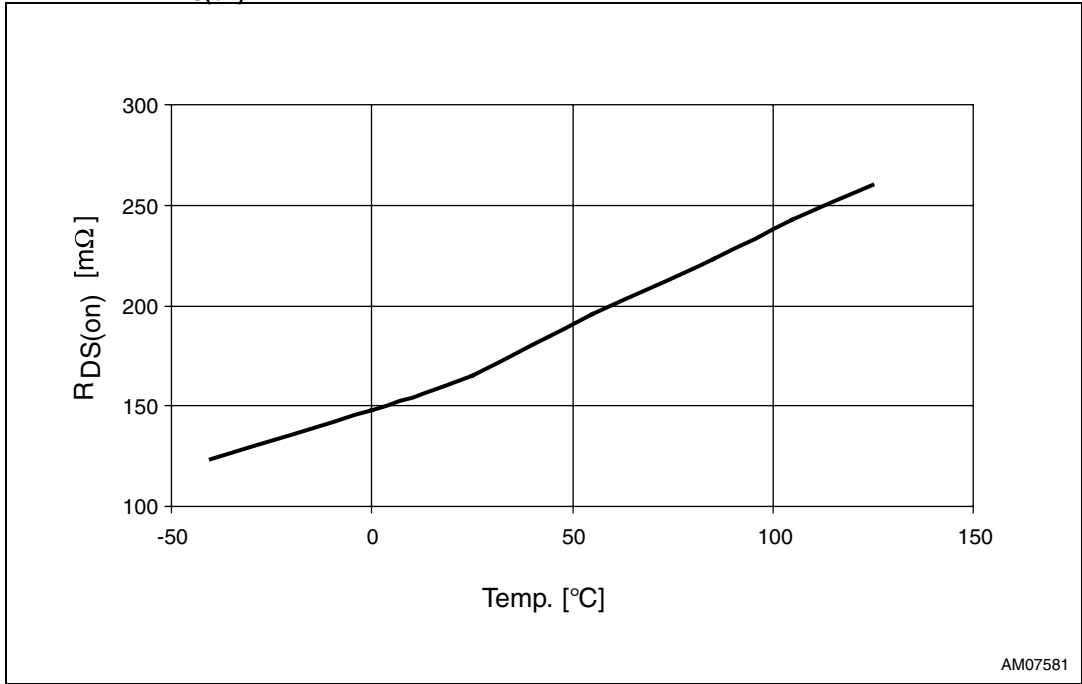


Figure 28. $V_{IL(\overline{EN})}$ vs. temperature

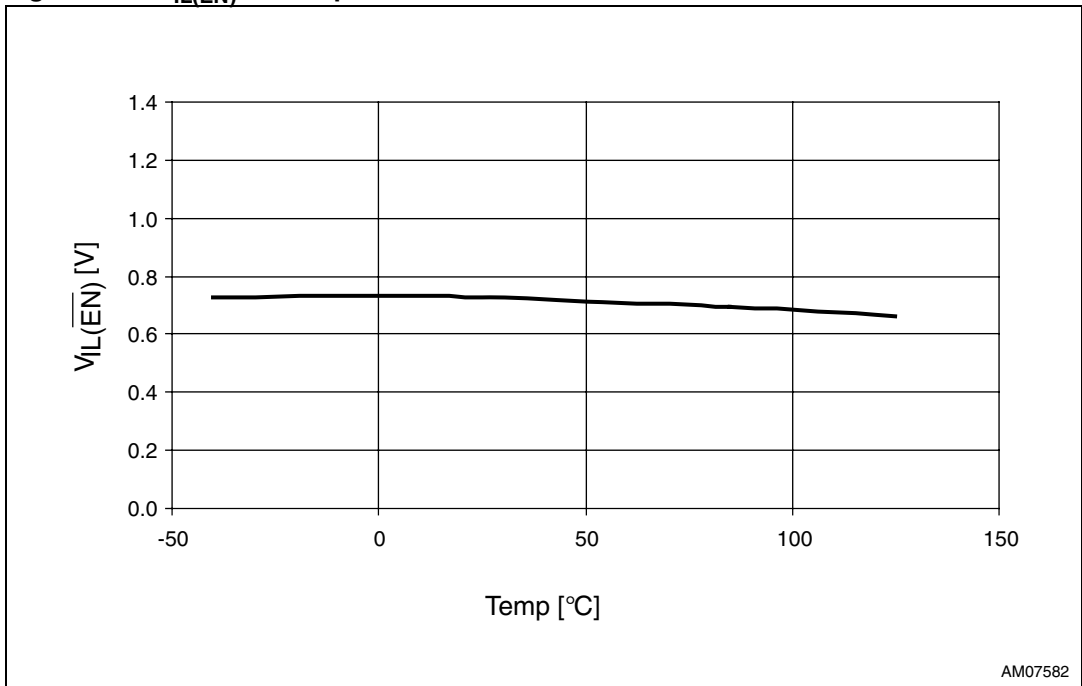


Figure 29. $V_{IH(\overline{EN})}$ vs. temperature

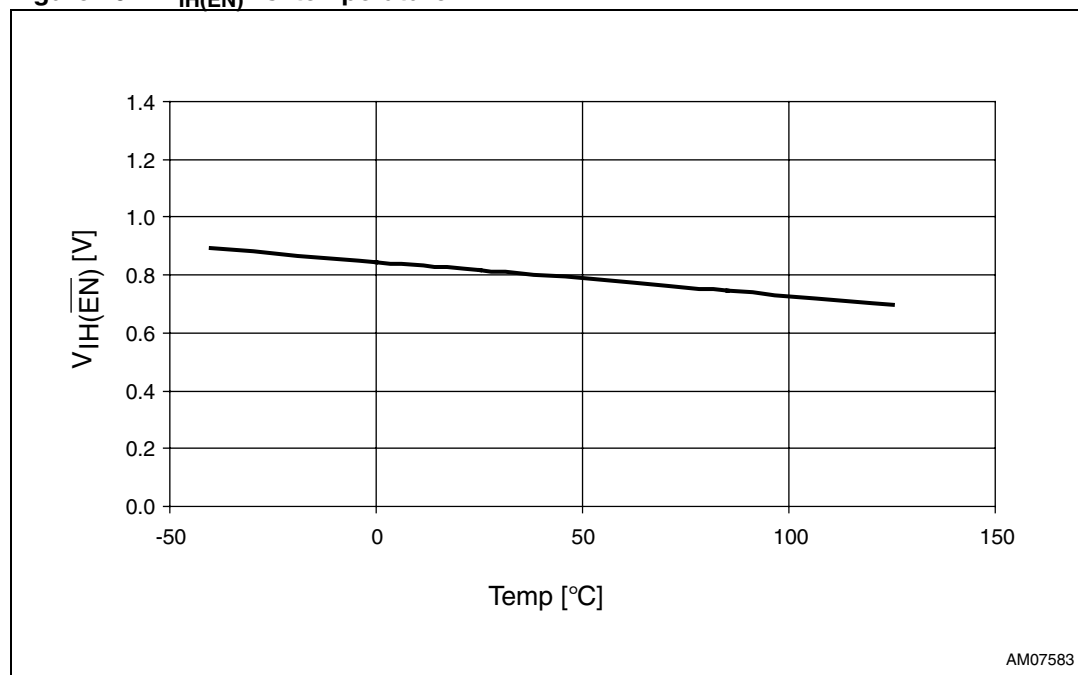


Figure 30. $I_{\overline{EN}}$ vs. V_{IN} at $V_{(\overline{EN})} = 5\text{ V}$

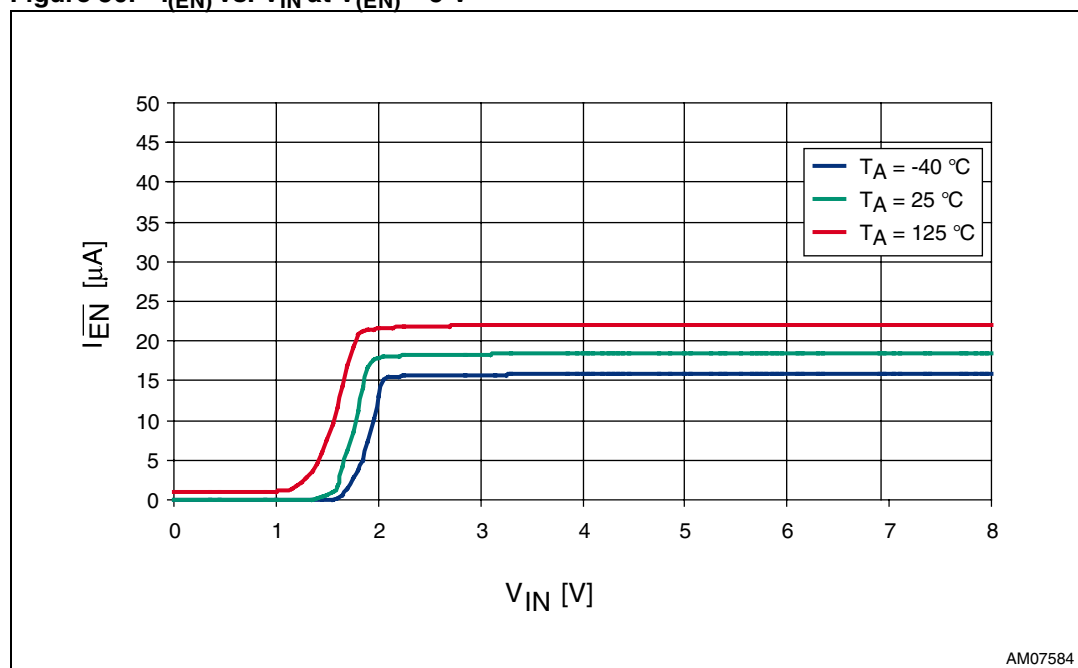


Figure 31. $R_{PD(\overline{EN})}$ vs. temperature at $V_{(\overline{EN})} = V_{IN} = 5\text{ V}$

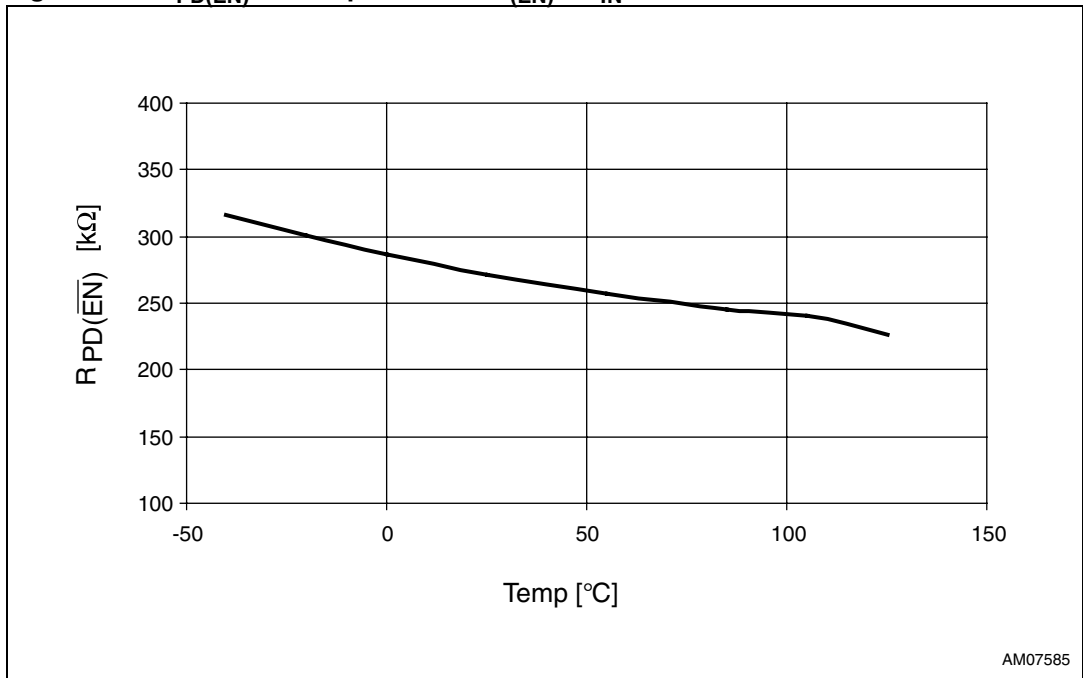


Figure 32. t_{on} vs. temperature

